

P-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) MAX.	I_D (A)	Q_g (TYP.)
-40	0.007at $V_{GS}=-10V$	-80	75nC

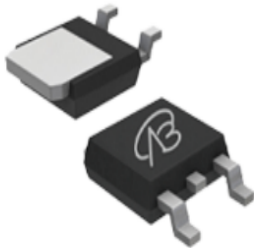
FEATURES

- SGT technology Power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested

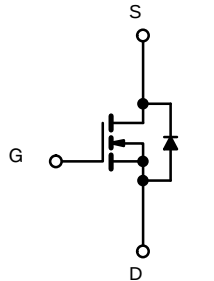


RoHS
COMPLIANT
HALOGEN
FREE

TO-252



Top View



P-Channel MOSFET

APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$)	I_D	$T_C = 25\text{ }^{\circ}\text{C}$ -80	A
		$T_C = 70\text{ }^{\circ}\text{C}$ -65	
Pulsed Drain Current ($t = 100\text{ }\mu\text{s}$)	I_{DM}	-240	
Avalanche Current	I_{AS}	-80	mJ
Single Avalanche Energy ^a		E_{AS} 655	
Maximum Power Dissipation ^a	P_D	$T_C = 25\text{ }^{\circ}\text{C}$ 150 ^b	W
		$T_C = 100\text{ }^{\circ}\text{C}$ 57 ^b	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	$^{\circ}\text{C/W}$
Junction-to-Case (Drain)	R_{thJC}	1.3	

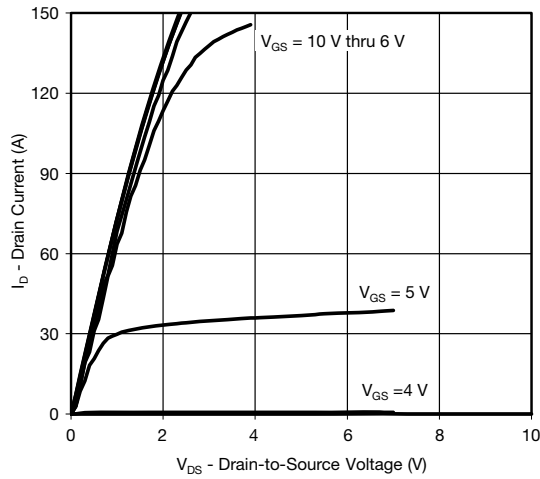
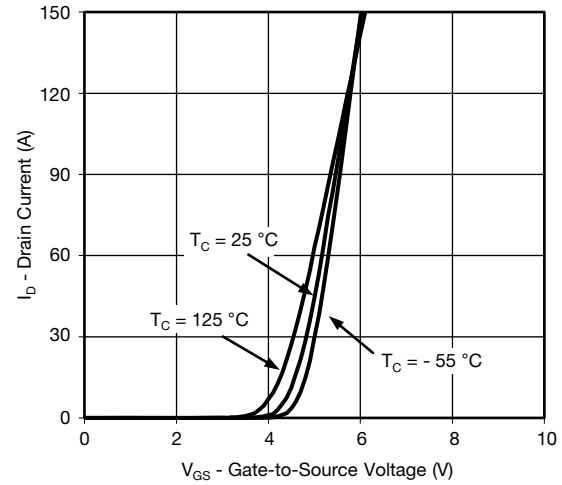
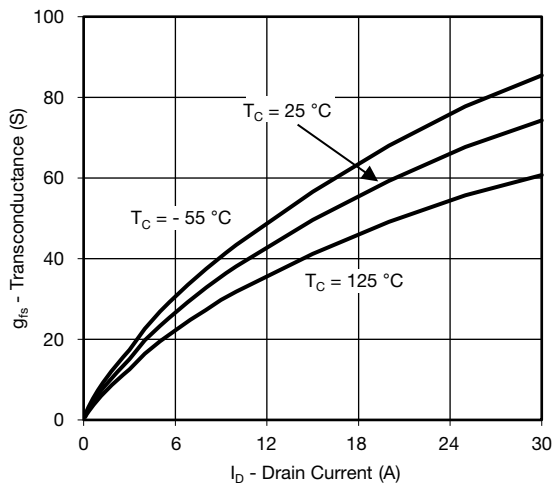
Notes

- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

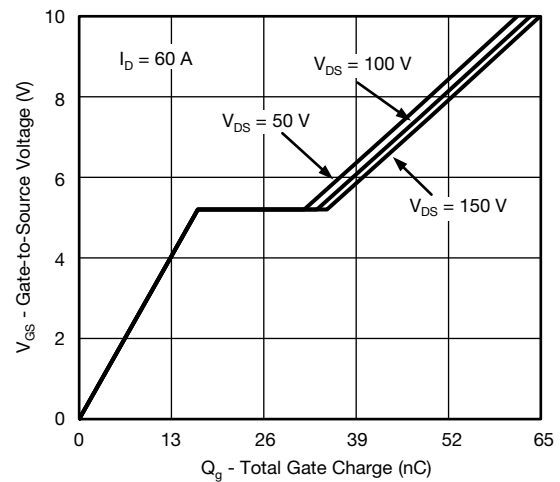
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	-40	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	-2.5	-	-4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -40 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -40 V, V _{GS} = 0 V, T _J = 125 °C	-	-	-150	
		V _{DS} = -40 V, V _{GS} = 0 V, T _J = 175 °C	-	-	-5	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = -10 V	-90	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V, I _D = -20 A	-	0.007	-	Ω
		V _{GS} = -4.5 V, I _D = -25A	-	0.015	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = -15 V, I _D = -20 A	-	75	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = -30 V, f = 1 MHz	-	8100	-	pF
Output Capacitance	C _{oss}		-	246	-	
Reverse Transfer Capacitance	C _{rss}		-	21	-	
Total Gate Charge ^c	Q _g	V _{DS} = -20 V, V _{GS} = -10 V, I _D = -60 A	-	75	96	nC
Gate-Source Charge ^c	Q _{gs}		-	16.7	-	
Gate-Drain Charge ^c	Q _{gd}		-	16.9	-	
Gate Resistance	R _g	f = 1 MHz	1.5	3	5	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = -20 V, R _L = 1.66 Ω I _D ≅ 60 A, V _{GEN} = -10 V, R _g = 1 Ω	-	14	25	ns
Rise Time ^c	t _r		-	114	203	
Turn-Off Delay Time ^c	t _{d(off)}		-	35	73	
Fall Time ^c	t _f		-	87	153	
Drain-Source Body Diode Ratings and Characteristics ^b (T _C = 25 °C)						
Pulsed Current (t = 100 μs)	I _{SM}		-	-	-280	A
Forward Voltage ^a	V _{SD}	I _F = -10 A, V _{GS} = 0 V	-	-0.8	-1.2	V
Reverse Recovery Time	t _{rr}	I _F = -30 A, di/dt = 100 A/μs	-	200	400	us
Peak Reverse Recovery Charge	I _{RM(REC)}		-	11	20	A
Reverse Recovery Charge	Q _{rr}		-	0.9	1.8	μC

Notes

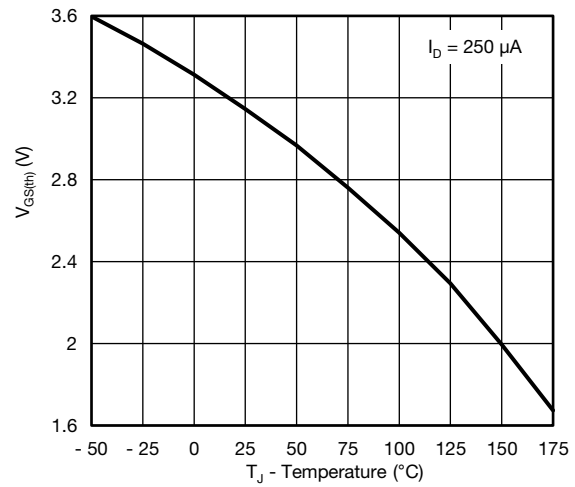
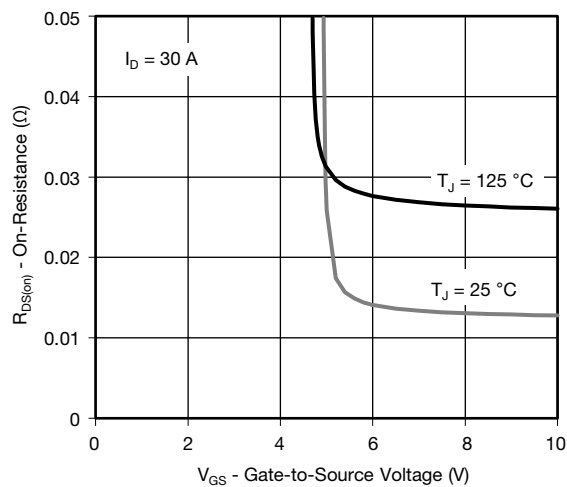
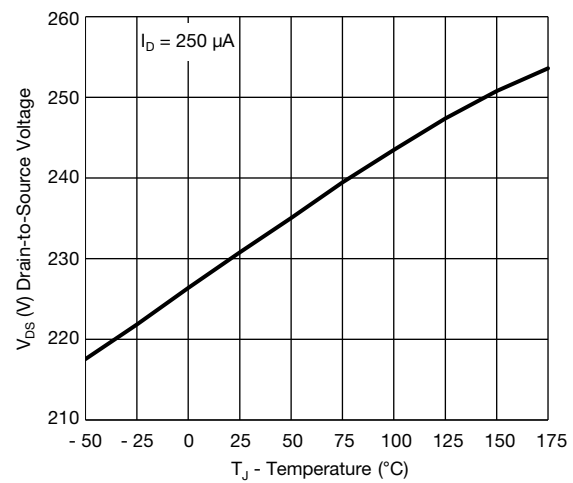
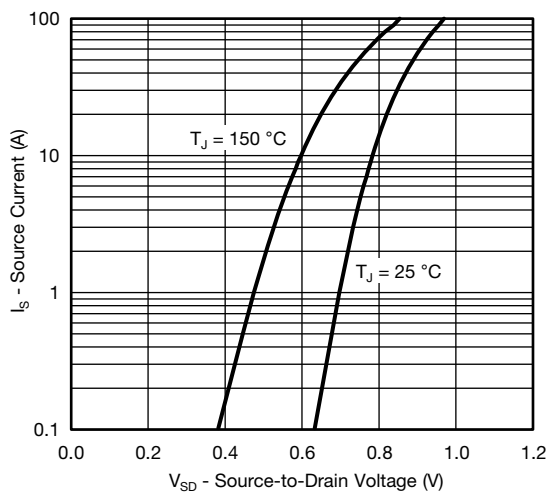
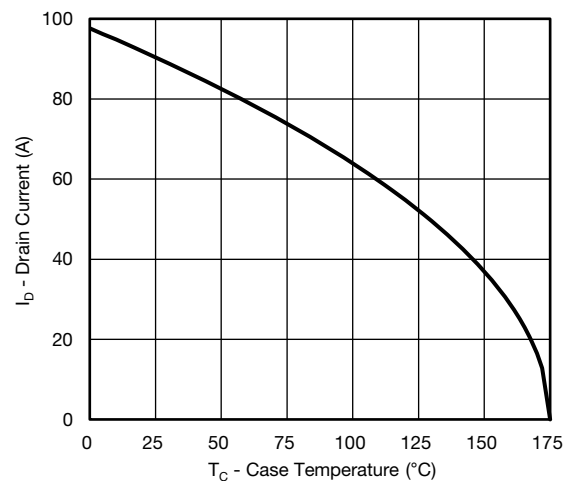
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

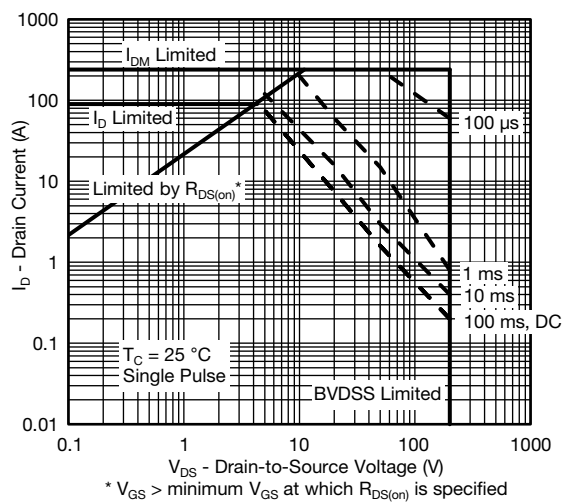
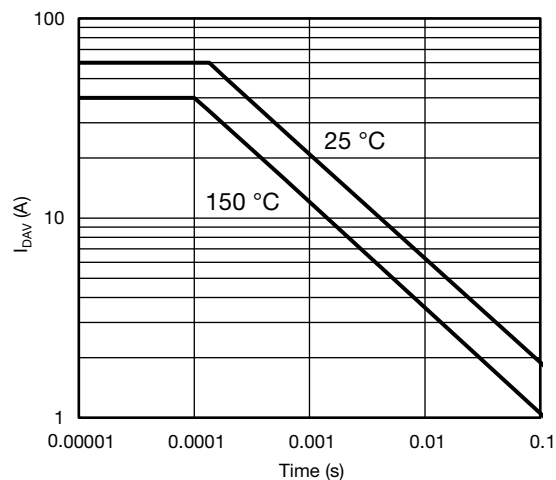
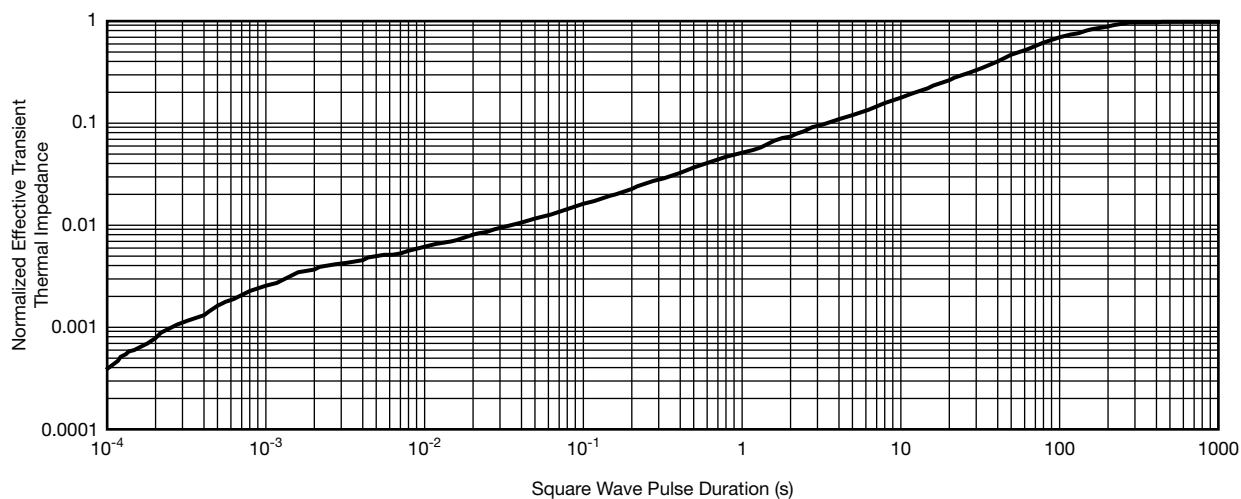
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

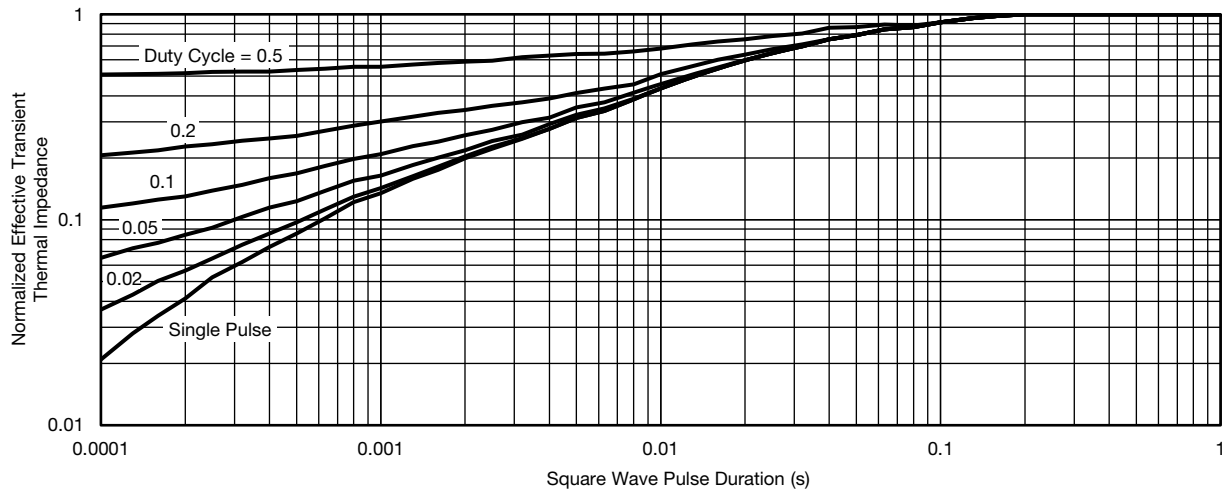
On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

Drain Source Breakdown vs. Junction Temperature

Source Drain Diode Forward Voltage

Current De-rating

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Safe Operating Area

Single Pulse Avalanche Current Capability vs. Time

Normalized Thermal Transient Impedance, Junction-to-Ambient

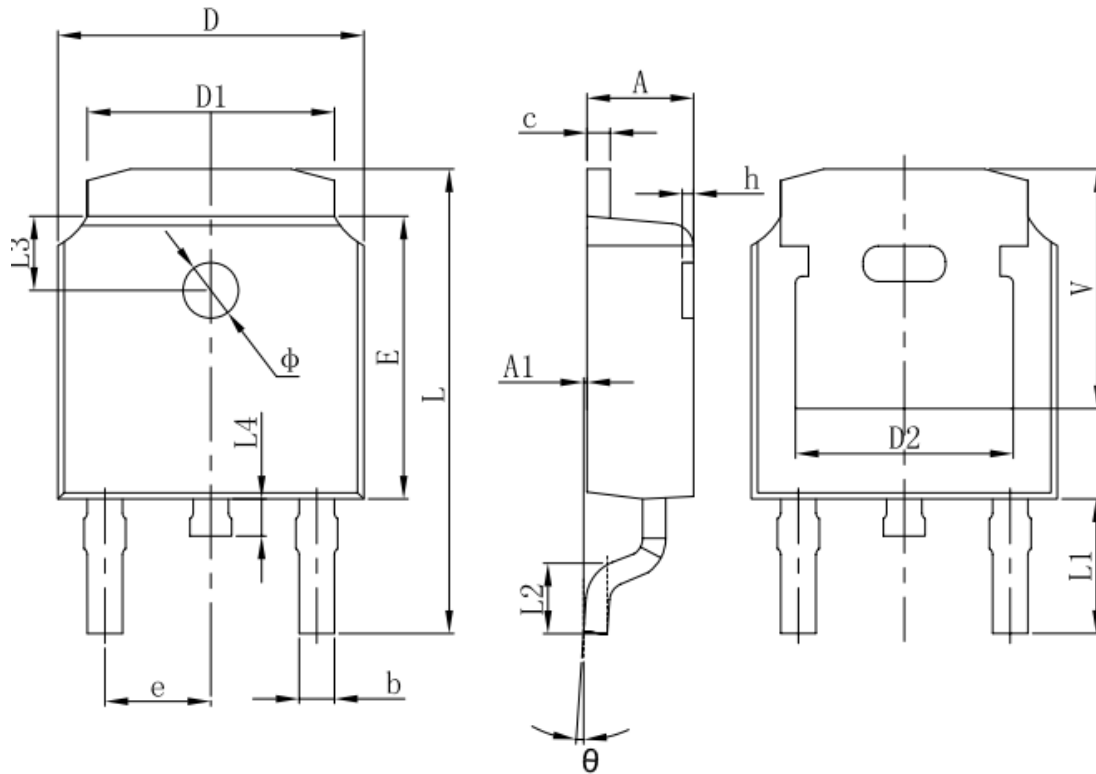
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

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